

SOLUTIONS TO PROBLEM SHEET 4

$$Q1) V_0 = \frac{kT}{e} \ln \left( \frac{p_p}{p_n} \right) = \frac{kT}{e} \ln \left( \frac{n_n}{n_p} \right)$$

$$\sigma_n = n_n e \mu_e \Rightarrow n_n = \frac{\sigma_n}{e \mu_e}$$

$$\sigma_p = p_p e \mu_h \Rightarrow p_p = \frac{\sigma_p}{e \mu_h}$$

$$\therefore n_p = \frac{n_i^2}{p_p} = \frac{n_i^2 e \mu_h}{\sigma_p}$$

$$V_0 = \frac{kT}{e} \ln \left( \frac{n_n}{n_p} \right) = \frac{kT}{e} \ln \frac{\sigma_n \sigma_p}{e \mu_e n_i^2 e \mu_h} = \frac{kT}{e} \ln \frac{\sigma_n \sigma_p}{e^2 n_i^2 \mu_e \mu_h}$$

$$= \frac{(1.38 \times 10^{-23})(300)}{1.6 \times 10^{-19}} \ln \frac{(10^4)(10^2)}{e^2 (2.5 \times 10^{19})^2 (0.36)(0.17)}$$

$$= \underline{0.358 \text{ V}} \quad \#$$

$$Q2) \text{ Transconductance, } g_m = \frac{\mu_e C_g V_{ds}}{\ell^2}; \text{ and } C_g = \frac{\epsilon A}{d}$$

$$\therefore g_m = \frac{\mu_e \epsilon_0 \epsilon_r V_{ds} A}{d \ell^2}$$

$$= \frac{(0.02)(8.854 \times 10^{-12})(3.7)(10)(0.84 \times 10^{-3})(5 \times 10^{-6})}{(5 \times 10^{-6})^2 (150 \times 10^{-9})}$$

$$= \underline{7.34 \times 10^{-3} \text{ S}} \quad \#$$

Q3)

$$I_d = \frac{\mu_e C_g}{e^2} \left( V_g - V_T - \frac{V_d}{2} \right) V_d ; \text{ and since } V_d \ll V_g$$

$$V_d \ll V_T$$

$$\Rightarrow I_d \approx \frac{\mu_e C_g}{e^2} (V_g - V_T) V_d$$

If  $V_g$  is fixed, we have  $\frac{V_d}{I_d} = \frac{e^2}{\mu_e C_g (V_g - V_T)} = R$

Rearranging;  $V_g = \frac{e^2}{\mu_e C_g R} + V_T$

$$= \frac{(5 \times 10^{-6})^2}{(0.02)(1 \times 10^{-12})(2 \times 10^3)} + 3$$

$$= \underline{3.625 \text{ V}}$$

#.

Possible disadvantages depend on precise applications, but  $R$  depends on  $V_g$ ; also depends on MOST characteristics which may be difficult to control; noise on  $V_g$  is also transferred to rest of the circuit; only a linear resistor for low  $V_d$ ; more complicated than a simple  $R$ .

Q4)  $I_d = \frac{\mu_e C_g}{e^2} \left( V_g - V_T - \frac{V_d}{2} \right) V_d$  in induced channel region

and  $I_{ds} = \frac{\mu_e C_g}{2e^2} (V_g - V_T)^2$  in saturated region } where  $V_d > V_g - V_T$

$g_m = \mu_e C_g (V_g - V_T) / e^2$  in saturated region

Substituting values,  $g_m = \frac{\mu_e C_g}{e^2} \sqrt{\frac{I_{ds} \cdot 2e^2}{\mu_e C_g}} = \frac{1}{e} \sqrt{2 I_{ds} \cdot \mu_e \cdot C_g}$

Hence;  $C_g = (e g_m)^2 / (2 I_{ds} \cdot \mu_e) = \frac{(10 \times 10^{-6} \cdot 2 \times 10^{-3})^2}{(2 \cdot 5 \times 10^{-3} \cdot 0.13)} = \underline{0.37 \text{ pF}}$  #.